

# FASTSWITCH EASY-TO-DRIVE (ETD) NPN TRANSISTORS

#### PRELIMINARY DATA

- HIGH SWITCHING SPEED NPN POWER TRANSISTORS
- EASY TO DRIVE
- HIGH VOLTAGE FOR OFF-LINE APPLICA-TIONS
- 100KHz SWITCHING SPEED
- LOW COST DRIVE CIRCUITS
- LOW DYNAMIC SATURATION

#### APPLICATIONS

- SMPS
- MOTOR DRIVES

#### DESCRIPTION

These Easy-to-Drive FASTSWITCH NPN power transistors are specially designed for high reliability

industrial and professional power driving applications such as motor drives and off-line switching power supplies. ETD transistors will operate using easy drive circuits at up to 100KHz; this helps to simplify designs and improve reliability. The superior switching performance and low crossover losses reduce dissipation and consequently lower the equipment operating temperature. These ETD transistors are suitable for application in high power, high reliability, motor drives and half bridge and full bridge converters.

These Easy-To-Drive FASTSWITCH transistors are available in TO-218 and TO-3 packages. Additionally, the alumina isolated version is available in the TOP-3I package.



#### ABSOLUTE MAXIMUM RATINGS

Symbol						
	Parameter TO-21 TOP-3 TO-3		BUF4 BUF42 BUF42	201 B	UF420A JF420A1 IF420AM	Unit
VCEV	Collector-emitter Voltage (VBE = - 1.5V)		850 1000		1000	V
VCEO	Collector-emitter Voltage (I <sub>B</sub> = 0)		450			V
VEBO	Emitter-base Voltage (I <sub>C</sub> = 0)		7			V
Ic	Collector Current		30			А
ICM	Collector Peak Current		60			А
I <sub>B</sub>	Base Current		6			A
IBM	Base Peak Current		9			А
			TO-3	TO-218	TOP-3I	
Piet	Total Dissipation at $T_c < 25^{\circ}C$		200	200	115	W
Tstg	Storage Temperature			- 65 to 150		
Τ,	Max. Operating Junction Temperature			°C		

## BUF420/420I/420M - BUF420A/420AI/420AM

#### THERMAL DATA

			TO-3	TO-218	TOP-31	
Rthj case	Thermal Resistance Junction-case	Max	0.63	0.63	1.09	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>1</sub> = $25^{\circ}$ C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICER	Collector Cutoff Current ( $R_{BE} = 5\Omega$ )	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ $T_c = 100^{\circ}C$			0.2	mA mA
CEV	Collector Cutoff Current	$V_{CE} = V_{CEV} V_{BE} = -1.5V$ $V_{CE} = V_{CEV} V_{BE} = -1.5V T_c = 100^{\circ}C$			0.2	mA mA
EBO	Emitter Cutoff Current (I <sub>C</sub> = 0)	$V_{EB} = 5V$			1	mA
CEO(sus)	Collector Emitter Sustaining Voltage	I <sub>C</sub> = 0.2A L = 25mH	450			V
V <sub>EBO</sub>	Emitter-base Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 50mA	7			V
V <sub>CE(sat)</sub> *	Collector-emitter Saturation Voltage	$ \begin{array}{c} I_{C} = 10A & I_{B} = 1A \\ I_{C} = 10A & I_{B} = 1A \\ I_{C} = 20A & I_{B} = 4A \\ I_{C} = 20A & I_{B} = 4A \end{array} \\ T_{c} = 100^{\circ}C \\ T_{c} = 1$		0.8 0.5	2.8	V V V V
V <sub>BE(sat)</sub> *	Base-emitter Saturation Voltage			0.9 1.1	1.5	V V V V
di <sub>c</sub> /dt	Rate of Rise of on-state Collector Current	$ \begin{array}{ll} V_{CC}=300V \ R_{C}=0 & t_{p}=3\mu s \\ I_{B1}=1.5A & T_{j}=25^{\circ}C \\ I_{B1}=1.5A & T_{j}=100^{\circ}C \\ I_{B1}=6A & T_{j}=100^{\circ}C \end{array} $	70 150	100		Avµs Avµs Avµs
V <sub>CE</sub> (3µs)	Collector-emitter Dynamic Voltage			2.1	8	V V
V <sub>CE</sub> (5µs)	Collector-emitter Dynamic Voltage			1.1	4	V V
ts tf tc	Storage Time Fall Time Cross Over Time			1 0.05 0.08		μs μs μs
ts tr tc	Storage Time Fall Time Cross Over Time				2 0.1 0.18	μs μs μs
V <sub>CEW</sub>	Maximum Collector Emitter Voltage without Snubber	$ \begin{array}{ll} I_{C} = 10A & V_{CC} = 50V \\ V_{BB} = -5V & R_{BB} = 0.6\Omega \\ V_{clamp} = 400V & I_{B1} = 1A \\ L = 0.25mH & T_{1} = 125^{\circ}C \end{array} $	500			V
ts tr tc	Storage Time Fall Time Cross Over Time			1.5 0.04 0.07		μs μs μs



Symbol	Parameter	Test (	Conditions	Min.	Тур.	Max.	Unit
ts ti t <sub>c</sub>	Storage Time Fall Time Cross Over Time	$I_{C} = 10A$ $V_{BB} = 0$ $V_{clamp} = 400V$ L = 0.25mH	$I_{B1} = 1A$			3 0.15 0.25	μs μs μs
Vcew	Maximum Collector Emitter Voltage without Snubber	$I_{C} = 10A$ $V_{BB} = 0$ $V_{clamp} = 400V$ L = 0.25mH	$I_{B1} = 1A$	500			V
ts t <sub>1</sub> t <sub>c</sub>	Storage Time Fall Time Cross Over Time	$I_{C} = 20A$ $V_{BB} = -5V$ $V_{clamp} = 400V$ $L = 0.12mH$			2.2 0.06 0.12		μs μs μs
ts tr tc	Storage Time Fall Time Cross Over Time	$I_{C} = 20A$ $V_{BB} = -5V$ $V_{clamp} = 400V$ $L = 0.12mH$	$V_{CC} = 50V$ $R_{BB} = 0.6\Omega$ $I_{B1} = 4A$ $T_{J} = 125 C$			3.5 0.12 0.3	μs μs μs
V <sub>CEW</sub>	Maximum Collector Emitter Voltage without Snubber	$I_{CWoff} = 30A$ $V_{BB} = -5V$ L = 0.08mH $T_1 = 125^{\circ}C$	I <sub>BI</sub> = 6A V <sub>CC</sub> = 50V R <sub>BB</sub> = 0.6Ω	400			V

## ELECTRICAL CHARACTERISTICS (continued)

Turn-on Switching Test Circuit.



(1) Fast electronic switch (2) Non-inductive Resistor

Turn-off Switching Test Circuit.



(1) Fast electronic switch(2) Non-inductive Resistor

(3) Fast recovery rectifier

Turn-on Switching Test Waveforms.



Turn-off Switching Waveforms (inductive load).



Reverse Biased Safe Operating Areas.





Forward Biased Safe Operating Areas.



Storage Time Versus Pulse Time.

